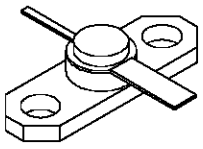
SGS-THOMSON MICROELECTRONICS

MSC82302

RF & MICROWAVE TRANSISTORS GENERAL PURPOSE AMPLIFIER APPLICATIONS

PRELIMINARY DATA

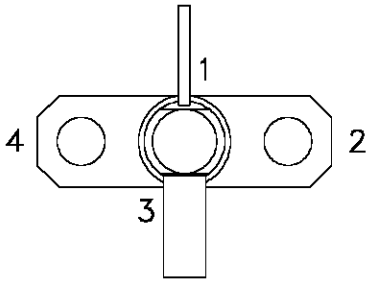
- REFRACTORY/GOLD METALLIZATION
- VSWR CAPABILITY 20:1 @ RATED CONDITIONS
- HERMETIC STRIPAC® PACKAGE
- P_{OUT} = 1.8 W MIN. WITH 10.0 dB GAIN



.250 2LFL (S010)
hermetically sealed

ORDER CODE	BRANDING
MSC82302	82302

PIN CONNECTION



1. Collector
2. Base
3. Emitter
4. Base

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DESCRIPTION

The MSC82302 is a common base hermetically sealed silicon NPN microwave power transistor utilizing a rugged overlay die geometry. This device is capable of withstanding 20:1 load VSWR at any phase angle under rated conditions.

The MSC82302 was designed for Class C Amplifier/Oscillator applications in the 1.5 - 2.3 GHz frequency range.

ABSOLUTE MAXIMUM RATINGS (T_{case} = 25°C)

Symbol	Parameter	Value	Unit
P_{DISS}	Power Dissipation* ($T_C \leq 50°C$)	6.0	W
I_C	Device Current*	300	mA
V_{CC}	Collector-Supply Voltage*	26	V
T_J	Junction Temperature	200	°C
T_{STG}	Storage Temperature	– 65 to +200	°C

THERMAL DATA

$R_{TH(j-c)}$	Junction-Case Thermal Resistance*	25	°C/W

*Applies only to rated RF amplifier operation

ELECTRICAL SPECIFICATIONS (T_{case} = 25°C)

STATIC

Symbol	Test Conditions		Value			Unit
			Min.	Typ.	Max.	
BV_{CBO}	I_C = 1mA	I_E = 0mA	44	—	—	V
BV_{EBO}	I_E = 1mA	I_C = 0mA	3.5	—	—	V
BV_{CER}	IC = 5mA	R_{BE} = 10Ω	44	—	—	V
I_{CBO}	V_{CB} = 22V		—	—	0.5	mA
h_{FE}	V_{CE} = 5V	I_C = 100mA	30	—	300	—

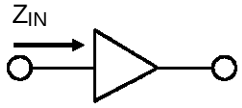
DYNAMIC

Symbol	Test Conditions			Value			Unit
				Min.	Typ.	Max.	
P_{OUT}	f = 2.3 GHz	P_{IN} = 0.18 W	V_{CC} = 22 V	1.8	—	—	W
ηc	f = 2.3 GHz	P_{IN} = 0.18 W	V_{CC} = 22 V	40	—	—	%
G_P	f = 2.3 GHz	P_{IN} = 0.18 W	V_{CC} = 22 V	10.0	—	—	dB
C_{OB}	f = 1 MHz	V_{CB} = 22 V		—	—	3.5	pF

IMPEDANCE DATA

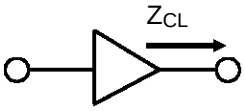
TYPICAL INPUT IMPEDANCE

Z_{IN}

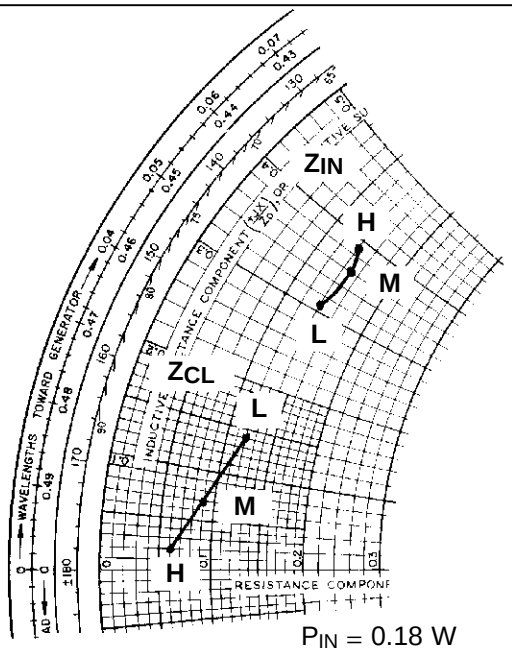


TYPICAL COLLECTOR LOAD IMPEDANCE

Z_{CL}



FREQ.	Z_{IN} (Ω)	Z_{CL} (Ω)
L = 2.0 GHz	7.0 + j 15.5	6.0 + j 7.0
M = 2.15 GHz	7.5 + j 18.0	4.5 + j 3.5
H = 2.3 GHz	7.0 + j 19.5	3.0 + j 1.0

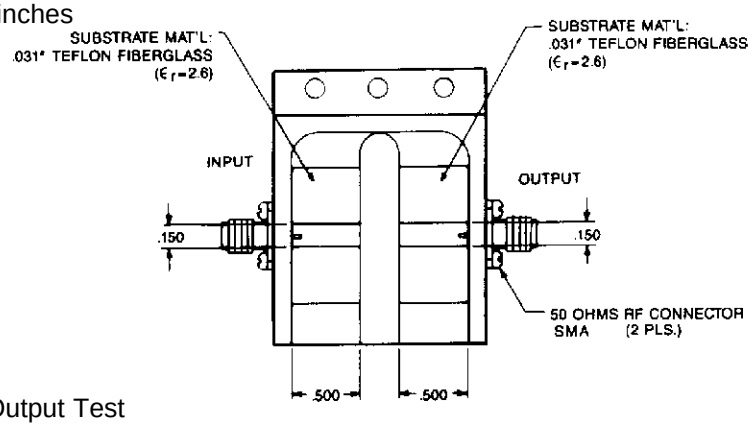


P_{IN} = 0.18 W
V_{CC} = 22 V
Normalized to 50 ohms

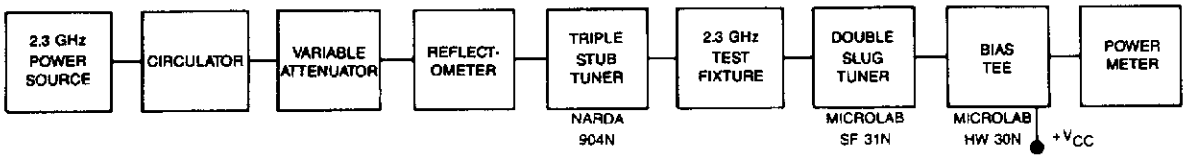
TEST CIRCUIT

Ref: Dwg. No. C125561

All dimensions are in inches
Frequency 2.3 GHz

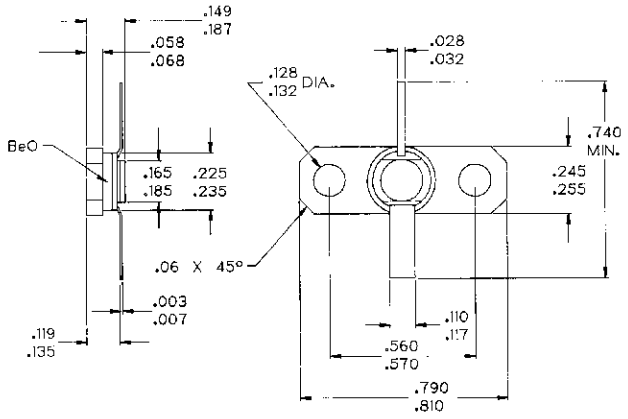


RF Amplifier Power Output Test



PACKAGE MECHANICAL DATA

Ref.: Dwg. No.: J135021C



NOTES:
1. ALL TOLERANCE ± .010 EXCEPT WHERE NOTED; DIMENSIONS IN INCHES.

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